

**Amendments to the Claims:**

This listing of the Claims will replace all prior versions and listings of the claims in this patent application.

**Listing of Claims:**

Claims 1-42. (canceled)

43. (new) A circuitry component comprising:

- a semiconductor substrate;
- a metallization structure over said semiconductor substrate;
- a silicon-nitride layer over said metallization structure;
- a circuit trace over said silicon-nitride layer; and
- a resistor connected to said circuit trace.

44. (new) The circuitry component as claimed in claim 43, wherein said resistor comprises silicon with a dopant of boron.

45. (new) The circuitry component as claimed in claim 43, wherein said resistor comprises silicon with a dopant of phosphorous.

46. (new) The circuitry component as claimed in claim 43, wherein said resistor comprises silicon with a dopant of arsenic.

47. (new) The circuitry component as claimed in claim 43, wherein said resistor comprises silicon with a dopant of gallium.

48. (new) The circuitry component as claimed in claim 43 further comprising a polymer layer between said silicon-nitride layer and said circuit trace.

49. (new) The circuitry component as claimed in claim 48, wherein said polymer layer comprises polyimide (PI).

50. (new) The circuitry component as claimed in claim 48, wherein said polymer layer comprises benzocyclobutene (BCB).

51. (new) The circuitry component as claimed in claim 43 further comprising a polymer layer on said circuit trace.

52. (new) The circuitry component as claimed in claim 51, wherein said polymer layer comprises polyimide (PI).

53. (new) The circuitry component as claimed in claim 51, wherein said polymer layer comprises benzocyclobutene (BCB).

54. (new) The circuitry component as claimed in claim 43, wherein said circuit trace comprises a copper layer.

55. (new) The circuitry component as claimed in claim 54, wherein said circuit trace further comprises a nickel layer over said copper layer.

56. (new) The circuitry component as claimed in claim 54, wherein said circuit trace further comprises a gold layer over said copper layer.

57. (new) The circuitry component as claimed in claim 54, wherein said circuit trace further comprises a titanium-containing layer under said copper layer.

58. (new) The circuitry component as claimed in claim 57, wherein said titanium-containing layer comprises tungsten.

59. (new) The circuitry component as claimed in claim 54, wherein said circuit trace further comprises a chromium-containing layer under said copper layer.

60. (new) The circuitry component as claimed in claim 43, wherein said circuit trace comprises a gold layer.

61. (new) The circuitry component as claimed in claim 60, wherein said circuit trace further comprises a titanium-containing layer under said copper layer.

62. (new) The circuitry component as claimed in claim 61, wherein said titanium-containing layer comprises tungsten.

63. (new) The circuitry component as claimed in claim 43, wherein said metallization structure comprises aluminum.

64. (new) A circuitry component comprising:  
multiple MOS devices;  
a metallization structure over said multiple MOS devices;  
a passivation layer over said metallization structure;  
a circuit trace over said passivation layer; and  
a resistor connected to said circuit trace.

65. (new) The circuitry component as claimed in claim 64, wherein said resistor comprises silicon with a dopant of boron.

66. (new) The circuitry component as claimed in claim 64, wherein said resistor comprises silicon with a dopant of phosphorous.

67. (new) The circuitry component as claimed in claim 64, wherein said resistor comprises silicon with a dopant of arsenic.

68. (new) The circuitry component as claimed in claim 64, wherein said resistor comprises silicon with a dopant of gallium.

69. (new) The circuitry component as claimed in claim 64 further comprising a polymer layer between said silicon-nitride layer and said circuit trace.

70. (new) The circuitry component as claimed in claim 69, wherein said polymer layer comprises polyimide (PI).

71. (new) The circuitry component as claimed in claim 69, wherein said polymer layer comprises benzocyclobutene (BCB).

72. (new) The circuitry component as claimed in claim 64 further comprising a polymer layer on said circuit trace.

73. (new) The circuitry component as claimed in claim 72, wherein said polymer layer comprises polyimide (PI).

74. (new) The circuitry component as claimed in claim 72, wherein said polymer layer comprises benzocyclobutene (BCB).

75. (new) The circuitry component as claimed in claim 64, wherein said circuit trace comprises a copper layer.

76. (new) The circuitry component as claimed in claim 75, wherein said circuit trace further comprises a nickel layer over said copper layer.

77. (new) The circuitry component as claimed in claim 75, wherein said circuit trace further comprises a gold layer over said copper layer.

78. (new) The circuitry component as claimed in claim 75, wherein said circuit trace further comprises a titanium-containing layer under said copper layer.

79. (new) The circuitry component as claimed in claim 78, wherein said titanium-containing layer comprises tungsten.

80. (new) The circuitry component as claimed in claim 75, wherein said circuit trace further comprises a chromium-containing layer under said copper layer.

81. (new) The circuitry component as claimed in claim 64, wherein said circuit trace comprises a gold layer.

82. (new) The circuitry component as claimed in claim 81, wherein said circuit trace further comprises a titanium-containing layer under said copper layer.

83. (new) The circuitry component as claimed in claim 82, wherein said titanium-containing layer comprises tungsten.

84. (new) The circuitry component as claimed in claim 64, wherein said metallization structure comprises aluminum.